

M27C4001

4096K (512K x 8) CMOS UV EPROM

PRELIMINARY DATA

- VERY FAST ACCESS TIME : 100ns.
- COMPATIBLE WITH HIGH SPEED MICRO-PROCESSORS, ZERO WAIT STATE.
- LOW POWER "CMOS" CONSUMPTION :
 - Operating current 70mA at 10 MHz
 - Standby current 100µA.
- PROGRAMMING VOLTAGE 12.75V.
- ELECTRONIC SIGNATURE FOR AUTOMATED PROGRAMMING.
- PROGRAMMING TIMES OF AROUND 48 SEC-ONDS (PRESTO II ALGORITHM).

DESCRIPTION

The M27C4001 is a high speed 4,194,304 (organized as 524,288 x 8 bit) ultraviolet erasable and programmable EPROM ideally suited for applications where fast turn-around and pattern experimentation are important requirements.

It is housed in a 32 pin Ceramic Frit Seal Window package. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.

PIN FUNCTIONS

A0-A18	ADDRESS INPUT
CE	CHIP ENABLE INPUT
OE	OUTPUT ENABLE
00-07	DATA INPUT/OUTPUT
VPP	PROGRAMMING VOLTAGE
Vcc	+5V POWER SUPPLY
GND	GROUND



Figure 1 : Pin Connection

N		h	VCC	
Vpp	1	32		
	2	31	A18	
	3	30	A17	
	4	29 🏻	A14	
	5	28	A13	
	6	27 🕽	A8	
A5	d 7	26	A9	
A4	8	25]	A11	
	9	24 🏻	OE	
A2	10	23	A10	
A1	d 11	22	CE	
AO	12	21 🛛	07	
00	13	20 🏻	06	
01	14	19	05	
02	15	18	04	
GND	16	17	03	

Figure 2 : Block Diagram



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
VI	Input or Output Voltages with respect to Ground	-0.6 to + 7.0	v
VPP	Supply Voltage with respect to Ground	-0.6 to + 14.0	V
V _{A9}	Voltage on A9 with respect to Ground	-0.6 to + 13.5	V
Vcc	Supply Voltage with respect to Ground	-0.6 to + 7.0	V
T _{bias}	Temperature range under bias	-10 to + 125	°C
T _{stg}	Storage temperature range	- 65 to + 150	°C

NOTE : Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may

OPERATING MODES

MODE	CE	OE	A9	VPP	OUTPUT
READ	L	L	X	X	D _{OUT}
OUTPUT DISABLE	L	н	X	X	HIGH Z
STANDBY	н	X	X	X	HIGH Z
PROGRAM	L	н	X	Vpp	D _{IN}
PROGRAM VERIFY	н	L	x	VPP	DOUT
PROGRAM INHIBIT	н	н	x	Vpp	HIGH Z
ELECTRONIC SIGNATURE	L	L	VH	Vcc	CODE

NOTE : X = Don't Care ; V_H = 12V ± 0.5V ; H = High ; L = Low



READ OPERATION DC AND AC CONDITIONS

SELECTION CODE	F 1	F6	F7	F3
Operating Temperature Range	0 to 70°C	-40 to 85°C	-40 to 105°C	-40 to 125°C
SELECTION CODE (Example for 0°C to 70°C Oper. Temp. Range)		, 15XF1, 20XF1, XF1	12F1, 15F1	, 20F1, 25F1
V _{CC} Power Supply	5V	± 5%	5V ±	: 10%

DC AND OPERATING CHARACTERISTICS

Symbol	Parameter	Test Condition	Val	Unit		
Symbol	r ai allielei	Test Condition	Min	Max	Onit	
lu	Input Leakage Current	$V_{IN} = 0V$ to V_{CC}	-1	1	μA	
ILO I	Output Leakage Current	$V_{IN} = 0V$ to V_{CC}	-1	1	μA	
ICC1	V _{CC} Active Current	$\overrightarrow{CE} = \overrightarrow{OE} = V_{IL}$, $I_{OUT} = 0$ mA (F = 10MHz)		70	mA	
Icc1	V _{CC} Active Current	$\overrightarrow{CE} = \overrightarrow{OE} = V_{IL}, I_{OUT} = 0 \text{ mA}$ (F = 5 MHz)		50	mA	
Icc2	VCC Standby Current - TTL	CE = VIH		1	mA	
lcc3	VCC Standby Current - CMOS	CE > V _{CC} -0.2V		100	μA	
IPP1	VPP Read Current	VPP = VCC		10	μA	
VIL	Input Low Voltage		-0.3	0.8	V	
VIH	Input High Voltage		2.0	Vcc+ 1.0	V	
VOL	Output Low Voltage	I _{OL} = 2.1 mA	1	0.45	V	
V _{OH}	Output High Voltage	lон = -400 μA lон = -100 μA	2.4 V _{CC} - 0.7		v v	

AC CHARACTERISTICS

Symbol		-		27C4001									
	Parameter	Test Condi- tion	-1	0	-1	12	-1	15	-1	20	-:	25	Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
tacc	Address to Output Delay	CE=OE=VIL		100		120		150		200		250	ns
tCE	CE to Output Delay	OE=VIL		100		120		150		200		250	ns
toe	OE to Output Delay	CE=VIL		50		60		60		70		100	ns
tor	OE High to Output Float	CE=VIL	0	30	0	40	0	50	0	80	0	80	ns
tон	Output hold from ad- dress	CE=OE=VIL	0		0		0		0		0		ns

CAPACITANCE⁽³⁾

 $(T_A = 25^{\circ}C 1, f = 1MHz)$

Symbol	Parameter	Test Condition	Max	Unit
CIN	Input Capacitance	V _{IN} = 0V	5	pF
Сол	Output Capacitance	V _{OUT} = 0V	5	pF

NOTES : 1. Vcc Must be applied simultaneously or before VPP and removed simultaneously or after VPP.

2. This parameter is only sampled and not 100 % tested. Output float is defined as the point where data is no longer driven (see timing diagram). 3. This parameter is only sampled and not 100 % tested.



M27C4001

AC TEST CONDITIONS

Output Rise and Fall Times	:	≤ 20 ns
Input Pulse Levels	:	0.45 to 2.4V

Timing Measurement Reference Levels : Inputs : 0.8 and 2V- Outputs : 0.8 and 2V



Figure 3 : AC Testing input/Output Waveform



Figure 5 : AC Waveforms



NOTES : 1. Typical values are for $T_A = 25^{\circ}C$ and nominal supply voltage.

2. This parameter is only sampled and not 100 % tested. 3. OE may be delayed up to t<u>CE</u> - t<u>OE</u> after the falling edge <u>CE</u> without impact on t<u>CE</u>. 4. t_{DF} is specified from <u>OE</u> or <u>CE</u> whichever occurs first.



DEVICE OPERATION

The modes of operations of the M27C4001 are listed in the Operating Modes table. A single 5V power supply is required in the read mode. All inputs are TTL levels except for VPP and 12V on A9 for Electronic Signature.

READ MODE

The M27C4001 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that the addresses are stable, the address access time (tacc) is equal to the delay from CE to output (tcE). Data is available at the output after a delay of toE has been low and the addresses have been stable for at least tacc-toE.

STANDBY MODE

The M27C4001 has a standby mode which reduces the active current from 50mA to 0.1mA. The M27C4001 is placed in the standby mode by applying a CMOS high signal to the CE input. When in the standby mode, the outputs are in a high impedance state, independent of the OE input.

TWO LINE OUTPUT CONTROL

Because EPROMs are usually used in larger memory arrays, this product features a 2 line control function which accommodates the use of multiple memory connection. The two line control function allows :

a) the lowest possible memory power dissipation,

b) complete assurance that output bus contention will not occur.

For the most efficient use of these two control lines, CE should be decoded and used as the primary device selecting function, while OE should be made a common connection to all devices in the array and connected to the READ line from the system control bus. This ensures that all deselected memory devices are in their low power standby mode and that the output pins are only active when data is required from a particular memory device.

SYSTEM CONSIDERATIONS

The power switching characteristics of CMOS-E4 EPROMs require careful decoupling of the devices.

The supply current, Icc, has three segments that are of interest to the system designer : the standby current level, the active current level, and transient current peaks that are produced by the falling and rising edges of CE. The magnitude of the transient current peaks is dependent on the capacitive and inductive loading of the device at the output. The associated transient voltage peaks can be suppressed by complying with the two line output control and by properly selected decoupling capacitors. It is recommended that a 1µF ceramic capacitor be used on every device between Vcc and GND. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7µF bulk electrolytic capacitor should be used between V_{CC} and GND for every eight devices. The bulk capacitor should be located near the power supply connection point. The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of PCB traces.

PROGRAMMING

Caution : exceeding 14V on VPP pin will permanently damage the M27C4001.

When delivered (and after each erasure for UV EPROM), all bits of the M27C4001 are in the "1" state. Data is introduced by selectively programming "0s" into the desired bit locations. Although only "0s" will be programmed, both "1s" and "0s" can be present in the data word. The only way to change a "0" to a "1" is by die exposition to ultraviolet light (UV EPROM). The M27C4001 is in the programming mode when V_{PP} input is at 12.75V, and CE is at TTL-low. The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL. V_{CC} is specified to be 6.25V \pm 0.25V.

PRESTO II PROGRAMMING ALGORITHM

PRESTO II Programming Algorithm allows the whole array to be programmed with a guaranteed margin, in a typical time of less than 48 seconds. Programming with PRESTO II consists of applying a sequence of 100 microseconds program pulses to each byte until a correct verify occurs. During programming and verify operation, a MARGIN MODE circuit is automatically activated in order to guarantee that each cell is programmed with enough margin. No overprogram pulse is applied since the verify in MARGIN MODE provides necessary margin to each programmed cell.



DEVICE OPERATION (Continued)

PROGRAM INHIBIT

Programming of multiple M27C4001s in parallel with different data is also easily accomplished. Except for CE, all like inputs including OE of the parallel M27C4001 may be common. A TTL low level pulse applied to a M27C4001's CE input, with VPP at 12.75V, will program that M27C4001. A high level CE input inhibits the other M27C4001s from being programmed.

PROGRAM VERIFY

A verify (read) should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with OE at V_{IL} , CE at V_{IH} , V_{PP} at 12.75V and Vcc at 6.25V.

ELECTRONIC SIGNATURE

The Electronic Signature mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment to automatically match the device to be programmed with its corresponding programming algorithm. This mode is functional in the $25^{\circ}C \pm 5^{\circ}C$ ambient temperature range that is required when programming the M27C4001. To activate this mode, the programming equipment must force 11.5V to 12.5V on address line A9 of the M27C4001 with $V_{PP} = V_{CC} = 5V$. Two iden-tifier bytes may then be sequenced from the device outputs by toggling address line A0 from VII to VIH. All other address lines must be held at VII during Electronic Signature mode. Byte 0 (A0=VIL) represents the manufacturer code and byte 1 ($A0=V_{IH}$) the device identifier code. For the SGS-THOMSON M27C4001, these two identifier bytes are given here below, and can be read-out on outputs O0 to O7.

ERASURE OPERATION (applies for UV EPROM)

The erasure characteristics of the M27C4001 is such that erasure begins when the cells are exposed to light with wavelengths shorter than approximately 4000 Angstrom. It should be noted that sunlight and some type of fluorescent lamps have wavelengths in the 3000-4000 Å range. Research shows that constant exposure to room level fluorescent lighting could erase a typical M27C4001 in about 3 years, while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the M27C4001 is to be exposed to these types of lighting conditions for extended periods of time, it is suggested that opaque labels be put over the M27C4001 window to prevent unintentional erasure. The recommended erasure procedure for the M27C4001 is exposure to short wave ultraviolet light which has wavelength 2537 Å. The integrated dose (i.e. UV intensity x exposure time) for erasure should be a minimum of 15 W-sec/cm2. The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with 12000 μ W/cm2 power rating. The M27C4001 should be placed within 2.5cm (1 inch) of the lamp tubes during the erasure. Some lamps have a filter on their tubes which should be removed before erasure.

IDENTIFIER					PI	NS				
	A0	07	06	05	04	03	02	01	00	Hex
MANUFACTURER CODE	VIL	0	0	1	0	0	0	0	0	20
DEVICE CODE	Vін	0	1	0	0	0	0	0	1	41

ELECTRONIC SIGNATURE

NOTE : A9 = 12V \pm 0.5V ; \overline{CE} = \overline{OE} = V_{IL} ; A1 to A8 = A10 to A18 = V_{IL} ; V_{CC} = V_PP = 5V



 $\begin{array}{l} \textbf{PROGRAMMING OPERATION} \\ (T_{A} = 25^{\circ}C \pm 5^{\circ}C, \ V_{CC}{}^{(1)} = 6.25V \pm 0.25V, \ V_{PP}{}^{(1)} = 12.75V \pm \ 0.25V) \end{array}$

DC AND OPERATING CHARACTERISTICS

Symbol	Parameter	Test Condition	Va	Unit	
Symbol	Falametei	(see note 1)	Min	Max	Omt
lu	Input Current (All Inputs)	$V_{IN} = 0V$ to V_{CC}	-10	+10	μ A
ViL	Input Low Level (All Inputs)		-0.1	0.8	v
VIH	Input High Level		2.4	V _{cc+} 0.5	v
VOL	Output Low Voltage During Verify	l _{OL} = 2.1 mA		0.45	v
V _{OH}	Output High Voltage During Verify	I _{OH} = -400µА	2.4		v
Icc2	V _{CC} Supply Current			50	mA
IPP2	VPP Supply Current (program)	CE = VIL		50	mA
VID	A9 Electronic Signature Voltage		11.5	12.5	v

AC CHARACTERISTICS

Symbol	Parameter	Parameter Test Condition	Va	lues	Unit
Symbol	Falanielei	(see note 1)	Min	Max	
tas	Address Setup Time		2		μs
toes	OE Setup Time		2		μs
tos	Data Setup Time		2		μs
tan	Address Hold Time		0		μs
tон	Data Hold Time		2		μs
tDFP(2)	Output Enable Output Float Delay		0	130	ns
tvps	VPP Setup Time		2		μs
tvcs	V _{CC} Setup Time		2		μs
tew	Initial Program Pulse Width		95	105	μs
t _{OE}	Data Valid from OE			100	ns

NOTES : 1. V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.

This parameter is only sampled and not 100 % tested. Output Float is defined as the point where data is no longer driven (see timing diagram).



PROGRAMMING OPERATION (Continued)

Figure 6 : Programming Waveforms



NOTES : 1. The input timing reference level is 0.8V for a VIL and 2V for a VIH.

2. to the and to the device but must be accommodated by the programmer. 3. When programming the M27C4001 a 0.1 μ F capacitor is required accross VPP and GND to suppress spurious voltage transients which can damage the device.



PROGRAMMING OPERATION (Continued)

Figure 7 : PRESTO II Programming Algorithm Flow Chart





ORDERING INFORMATION (UV EPROM)

Part Number	Access Time	Supply Voltage	Temp.Range	Package
M27C4001-10XF1	100 ns	5V ± 5%	0 to + 70°C	FDIP32-W
M27C4001-12XF1	120 ns	5V ± 5 %	0 to + 70°C	FDIP32-W
M27C4001-15XF1	150 ns	5V ± 5 %	0 to + 70°C	FDIP32-W
M27C4001-20XF1	200 ns	5V ± 5 %	0 to + 70°C	FDIP32-W
M27C4001-25XF1	250 ns	5V ± 5%	0 to + 70°C	FDIP32-W
M27C4001-12F1	120 ns	5V ± 10 %	0 to + 70°C	FDIP32-W
M27C4001-15F1	150 ns	5V ± 10 %	0 to + 70°C	FDIP32-W
M27C4001-20F1	200 ns	5V ± 10 %	0 to + 70°C	FDIP32-W
M27C4001-25F1	250 ns	5V ± 10 %	0 to + 70°C	FDIP32-W

PACKAGE MECHANICAL DATA

Figure 8 : 32-PIN WINDOW CERAMIC DUAL IN LINE FRIT-SEAL (F)



